

Simultaneously optimizing the interdependent thermoelectric parameters in $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$

Peijie Sun,^{*} Tsuyoshi Ikeno, Toshio Mizushima, and Yosikazu Isikawa[†]*Department of Physics, Toyama University, Toyama 930-8555, Japan*

(Received 17 August 2009; published 17 November 2009)

Substitution of Cu for Ni in the Kondo lattice system CeNi_2Al_3 results in a simultaneous optimization of the three interdependent thermoelectric parameters: thermoelectric power, electrical, and thermal conductivities, where the electronic change in conduction band induced by the extra electron of Cu is shown to be crucial. The obtained thermoelectric figure of merit zT amounts to 0.125 at around 100 K, comparable to the best values known for Kondo compounds. The realization of ideal thermoelectric optimization in $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$ indicates that proper electronic tuning of Kondo compounds is a promising approach to efficient thermoelectric materials for cryogenic application.

DOI: [10.1103/PhysRevB.80.193105](https://doi.org/10.1103/PhysRevB.80.193105)

PACS number(s): 72.20.Pa, 71.27.+a

Thermoelectric (TE) materials are used to construct all solid-state power generator or Peltier cooler. Current TE materials such as $\text{Bi}_2\text{Te}_3\text{-Sb}_2\text{Te}_3$ alloy have a dimensionless figure of merit $zT \sim 1$ at near or above room temperature.¹ zT , defined as $TS^2/\rho\kappa$, determines the efficiency of TE conversion at a particular temperature T , with S being the thermoelectric power, ρ the electrical resistivity, and κ the thermal conductivity which consists of electronic part κ_e and lattice part κ_L . In normal metals or semiconductors, S , ρ , and κ are not independent. The classical route to high-efficiency TE materials is based on doping or alloying an appropriate semiconductor into a degenerate regime of carrier concentration $n \sim 10^{19} \text{ cm}^{-3}$, where a good compromise between S and ρ is reached with a high thermoelectric power factor S^2/ρ .¹ Modern electronic technology has created a strong demand for TE materials operating at cryogenic temperatures, to provide applications such as spot cooling microelectronic superconducting devices. The aforementioned concept, unfortunately, does not seem to hold true for development of TE materials below 200 K.²

One promising candidate for cryogenic TE application is heavy-fermion (HF) or intermediate-valence (IV) metals, which are characterized by the so-called Kondo resonance of conduction electrons screening the magnetic moment of f or d electrons. Kondo resonance produces a sharp feature in the electronic density of states (DOS), leading to a 2–3 orders of magnitude enhancement of the effective charge-carrier mass m^* and a large S amounting to several tens of $\mu\text{V}/\text{K}$ at around Kondo temperature T_K .³ As metals, they have relatively large κ_e that is tied to metallic ρ by Wiedeman-Franz law ($\rho\kappa_e/T=L_0$, with $L_0=2.44 \times 10^{-8} \text{ V}^2/\text{K}^2$). A simple calculation neglecting κ_L indicates that $S > 156 \mu\text{V}/\text{K}$ is necessary to achieve a practical zT above unity. The largest S so far known in metallic Kondo systems is $\sim 120 \mu\text{V}/\text{K}$ observed in CePd_3 , with $zT < 0.25$ at around 200 K.^{1,4} Further enhancement of zT was not achieved for HF or IV systems, though a value as high as 14 has been predicted.⁵

Like the current TE materials in use, high- zT materials for cryogenic application might emerge by optimizing an appropriate parent system. The key point, therefore, is to identify this system and the mechanisms that might lead to optimization of the TE parameters. In this Brief Report, we report a simultaneous optimization of S , ρ , and κ_L in a Kondo lattice system $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$ realized by substitution. The Ce

ion in CeNi_2Al_3 experiences a nearly tetravalent^{6,7} or IV state,⁸ which, by replacing Ni with Cu, an atom with larger volume as well as an extra conduction electron, evolves into HF and eventually magnetically ordered state. The evolution accompanies an enhancement of the maximum thermoelectric power (Fig. 1, lower panel) and its shift to lower temperature. Concomitant reductions in ρ and κ_L due to the electronic change in conduction band and the chemical disorder, respectively, are also realized, resulting in a substantially enhanced $zT \sim 0.125$ at around 100 K. The largely enhanced electronic specific-heat coefficient γ and $\alpha=S/T$ ($T \rightarrow 0 \text{ K}$) (Fig. 1, upper panel) point to the formation of heavy quasiparticles with substitution. At below 100 K, the observed zT values largely exceed that of CePd_3 , the so-called “best” TE material in Kondo systems.⁴ The decisive impetus for the simultaneous optimization of S , ρ , and κ_L is to be discussed in terms of the electronic change in conduction band. A further development of more efficient TE materials for cryogenic application along the lines should be largely expected.

Polycrystalline $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$ compounds with various x were prepared by arc-melting stoichiometric amounts of constituent elements in a high-purity argon atmosphere. The purities of the starting elements are 99.9%, 99.997%, 99.999%, and 99.999% for Ce, Ni, Cu, and Al, respectively. No annealing treatment was carried out. Power x-ray diffraction spectra confirmed the formation of the hexagonal PrNi_2Al_3 -type structure of the samples with $x < 0.5$, with tiny impurity peak appearing at around $2\theta \sim 50^\circ$ as reported previously.^{6,9} For $x > 0.5$, a trace of second phase, which was determined to be CeCuAl_3 ,¹⁰ appears gradually. The second phase in the sample of $x=0.6$, i.e., the upper substitution limit in this work, was estimated to be less than 3%. For this composition, a magnetic transition was observed at 2.3 K and it increases rapidly with x . The continuous expansions of the lattice constants a and c (Fig. 1, inset) indicate successful substitution of Cu atoms. A change in the slopes of a and c as a function of x is discerned at around $x=0.4$, the critical concentration between the nonmagnetic and magnetic regimes.¹¹ The thermoelectric properties were measured by either a home-built cryostat with a slowly varying-gradient technique (chromel/Au+0.07% Fe thermocouple as ΔT detector) or a commercial physical properties measurement system [physical property measurement system (PPMS), Quantum Design]. The discrepancies between the two tech-

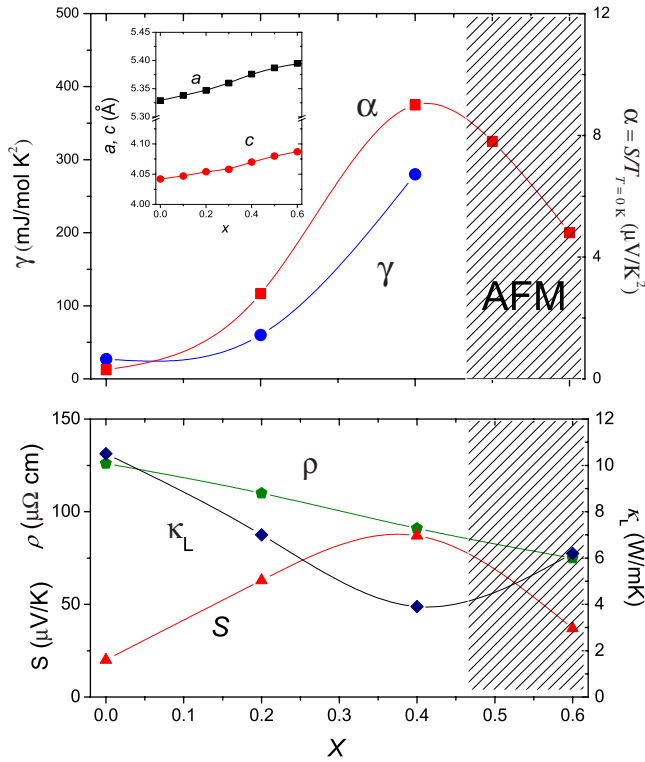


FIG. 1. (Color online) Upper panel: x dependence of γ and α , the zero-temperature linear coefficients of electronic specific heat and thermoelectric power of $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$, respectively. The enhancement of both quantities with x indicates the formation of heavy-fermion state with enhanced effective charge-carrier mass m^* . Lower panel: x dependence of the three thermoelectric parameters S , ρ , and κ_L at $T=100$ K. Their simultaneous optimization with increasing x results in an enhanced thermoelectric figure of merit at $x=0.4$. For the compounds with $x>0.5$, antiferromagnetic (AFM) order is confirmed. Inset shows smooth increase in the lattice parameters a and c as a function of x .

niques were found in less than 5% with a typical sample dimension of $1 \times 1 \times 5 \text{ mm}^3$.

The most impressive feature in the $S(T)$ curves (Fig. 2) is a largely enhanced, positive maximum S_{max} , as observed in many other Ce-contained HF or IV compounds.¹ For $x \leq 0.4$, while the position of S_{max} in temperature decreases, its value increases largely with x . The enhanced S_{max} value for the compound of $x=0.4$, $90 \mu\text{V/K}$ at 70 K, was confirmed by the two measurement techniques given above. The previous studies on annealed samples presented a S_{max} of only $60 \mu\text{V/K}$ for $x=0.4$.⁹ The difference with the present results most likely reflects the sensitivity of electron-electron correlations with respect to composition in the vicinity of the critical concentration: for example, γ and α show dramatic change at around $x=0.4$ (Fig. 1, upper panel). Looking carefully into the previous results,⁹ one also notice that the real S_{max} for $x=0.4$ could be higher: while γ doubles by varying x from 0.3 to 0.4 , α does not follow γ but remains flat. As estimated from the value of $1/\gamma$ and the position of S_{max} , Kondo temperature T_K decreases gradually with x . The enhancement of S_{max} with x tracks the enhancement of the effective mass m^* ($\sim \gamma$) as a consequence of the reduction in

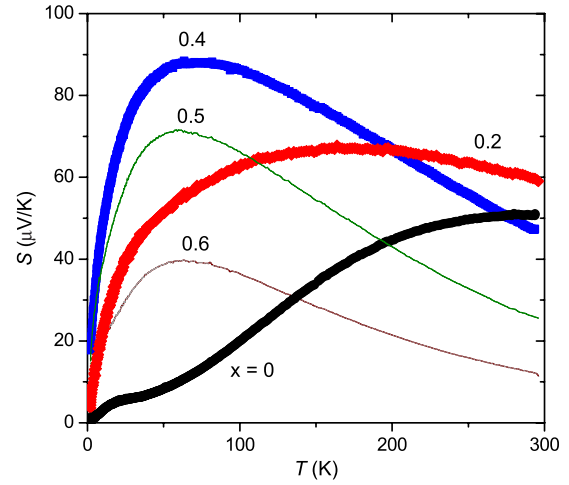


FIG. 2. (Color online) The thermoelectric power S as a function of temperature for various $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$ compounds. While the position of S_{max} in temperature decreases with substitution up to $x=0.4$, its value increases largely. Above this critical concentration, the compounds order magnetically and their S_{max} decreases dramatically with x .

T_K . The correspondence of the enhanced γ and α (Fig. 1, upper panel) follows the general behavior expected for correlated systems,^{12,13} unambiguously evidencing the realization of HF state. Further substitution exceeding $x=0.4$ reduces S_{max} , due to the onset of magnetic ordering and the consequent diminish of m^* .

Upon increasing x from 0.0 to 0.6 , the electrical resistivity ρ (Fig. 3, upper panel) evolves from a monotonically increasing to a monotonically decreasing function of temperature, again pointing to the decrease in T_K . The broad maximum in $\rho(T)$, another estimate of T_K , shifts from ~ 200 K for $x=0.2$ to ~ 100 K for $x=0.4$. Remarkably, ρ above 70 K exhibits a systematic reduction with increasing x , in spite of the increasing residual resistivity ρ_0 . In combination with the enhancement of S_{max} , this indicates a simultaneous optimization of ρ and S_{max} that is impossible in classical metals.

The overall resistivity of a nonmagnetic isoelectronic reference system $\text{La}(\text{Pd}_{1-x}\text{Ag}_x)_2\text{Al}_3$ (Ref. 14) exhibits behaviors characteristic of a normal metal and decreases steadily with increasing x (inset of Fig. 3). For instance, ρ at room temperature changes from $150 \mu\Omega \text{ cm}$ for $x=0.0$ to $35 \mu\Omega \text{ cm}$ for $x=0.6$, reflecting the electronic-structure change in the conduction band. The evolution of ρ in the reference system hints that the decrease in ρ with x in $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$ shares the same origin: it is due to a decrease in the usual electron-phonon-scattering term ρ_p , assuming that $\rho = \rho_0 + \rho_p + \rho_m$, where ρ_0 is the residual resistivity and ρ_m is the magnetic part occurring only in the Ce compounds. On the other hand, γ diminishes with x in $\text{La}(\text{Pd}_{1-x}\text{Ag}_x)_2\text{Al}_3$,¹⁵ indicative that the full-filled d band of Cu triggers a shift of the Fermi level away from the enhanced DOS of d character. Similar effect is confirmed both experimentally and theoretically in $\text{Ce}(\text{Pd}_{1-x}\text{Cu}_x)_2\text{Si}_2$.¹⁶ The shift of conduction band from d - to s - or p -like bands can naturally account for the decrease in ρ , as well as the decrease in $T_K \sim \exp[-1/\text{DOS}(\epsilon_F)J]$, as a function of x in $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$. $\rho(T)$ for $x=0.4$ shows an up-

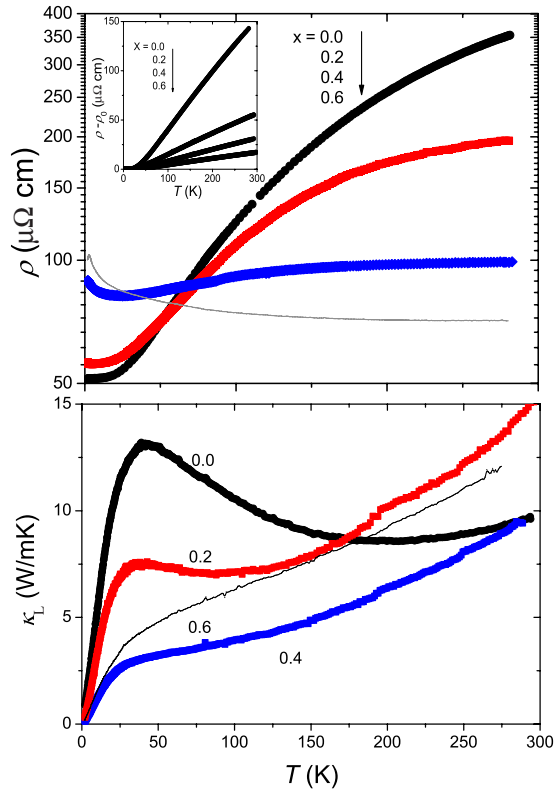


FIG. 3. (Color online) The electrical resistivity, ρ (upper panel), and the lattice contribution to thermal conductivity, κ_L (lower panel), as a function of temperature for various $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$ compounds. For the estimation of κ_L , the Wiedemann-Franz law and the Sommerfeld value of L were employed. Inset shows $\rho - \rho_0(T)$ of a reference system, $\text{La}(\text{Pd}_{1-x}\text{Ag}_x)_2\text{Al}_3$, which follows the Bloch-Grüneisen function typical of normal metals with a remarkable reduction in the overall values with increasing x . The residual resistivity ρ_0 of the reference compounds is 3.9, 28.9, 18.8, and 17.2 $\mu\Omega$ cm for $x=0.0, 0.2, 0.4$, and 0.6, respectively.

turn below 20 K as well as a broad hump at 100 K. This is a sign of the crystal electric field splitting effect on the sixfold-degenerate Ce^{3+} state, indicating that not only the ground Kramers doublet, but also one excited multiplet are perhaps involved in the transport properties. The ground-state degeneracy was only recently recognized to be important for TE properties in Kondo systems.¹⁷

The lattice thermal conductivity κ_L in CeNi_2Al_3 (Fig. 3, lower panel) is characterized by a maximum at $T \approx 40$ K, a fingerprint of crystalline solid. The κ_L maximum smears out with substituting Cu, leading to a largely reduced κ_L for $x=0.4$ over the whole temperature range. The reduction in κ_L is attributed to the substitutional chemical disorder that is frequently employed in modern TE development. To better understand the evolution of κ_L with x in the present system, however, it is necessary to consider another phonon-scattering process by, i.e., valence fluctuation, which was recently shown to be an effective way to reduce κ_L in HF or IV systems.¹⁸ The decrease in Kondo temperature T_K with x in the present system evidences the decrease in phonon-scattering rate by valence fluctuation, which gives the reason why κ_L of $x=0.6$ is higher than that of $x=0.4$. Furthermore,

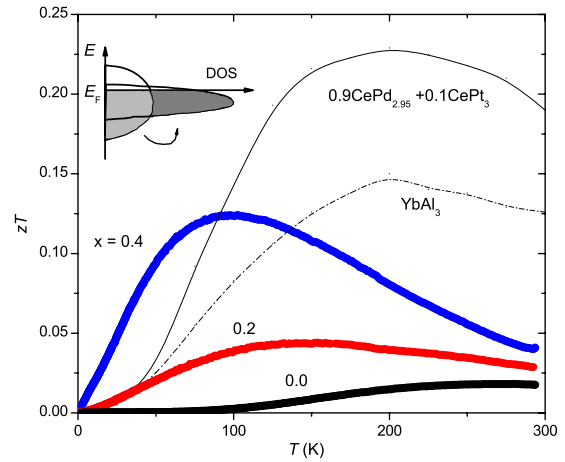


FIG. 4. (Color online) The dimensionless thermoelectric figure of merit zT of $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$, in comparison to that of optimized CePd_3 and YbAl_3 .⁴ Inset illustrates the evolution of the DOS of heavy quasiparticles at near the Fermi level from IV to HF state, which in principle accounts for the enhancement of S in the present $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$ system.

it should be noticed that the increase in κ_L with temperature for the substituted compounds is not typical of a crystalline solid, and instead is reminiscent of the typical κ_L observed in amorphous systems.

The simultaneous optimization of S , ρ , and κ_L realized in the present substitutional $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$ leads to a systematic substantial enhancement of zT values, as well as a shift of the zT maximum to lower temperature (Fig. 4). In particular at $T=100$ K, S is enhanced by a factor of 4.3 by varying x from 0.0 to 0.4, together with a reduction in ρ and κ_L by a factor of 1.5 and 2.7, respectively (Fig. 1, lower panel). At this temperature zT for $x=0.4$ assumes its peak with $zT_{\text{max}}=0.125$, amounting to half of the maximum zT value observed in optimized CePd_3 .⁴ Much higher zT than that of CePd_3 is observed at below 100 K in the present system. Comparing the zT values of $x=0.4$ to that of $x=0.0$ ($zT_{\text{max}} < 0.02$ at 280 K) reveals that the enhancement of zT is considerably significant. Noticeably, the most important among our observations is that the enhancement of S_{max} concomitant to the reduction in T_K is not specific to the present system. This is a general expectation for HF or IV systems without magnetic ordering,¹⁹ and has been confirmed in different systems such as $\text{Ce}(\text{Ni}_x\text{Pd}_{1-x})_2\text{Si}_2$,²⁰ though not as apparent as in $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$.

An independent control of S , ρ , and κ_L has been theoretically shown to be feasible by confining electrons into a low-dimensional system, and properly fabricated thin-film superlattice or nanowire indeed show enhanced thermoelectric properties.²¹ By contrast, the simultaneous optimization of the three interdependent thermoelectric parameters in $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$, in particular of S and ρ , is owing to the local interaction between the f and conduction bands. The substitution of Cu for Ni in CeNi_2Al_3 modifies the d -like conduction band with enhanced DOS to s - or p -like bands with charge carriers that are much more mobile. This modification on conduction band leads to not only an increase in electrical conductivity but also an enhancement of the Kondo

resonance peak in the DOS of the heavy quasiparticles (inset of Fig. 4) due to reduction in T_K , the latter being crucial for the enhancement of S that measures the energy derivative of DOS at the Fermi level. Further enhancement of the thermoelectric figure of merit in $\text{Ce}(\text{Ni}_{1-x}\text{Cu}_x)_2\text{Al}_3$ seems achievable through (i) substitution with heavier atoms instead of Cu, such as Ag, to further reduce κ_L , or (ii) approaching the best substitution amount in the vicinity of the critical concentration, $x=0.4$. Along the same lines, we also stress the significance to study other Kondo compounds which already exhibit moderately enhanced zT , for example, CePd_3 or systems with large ground-state degeneracy. It should be re-

mindful that for cryogenic application a comparable efficiency as for high-temperature application is not necessarily crucial; a moderately enhanced zT might make a significant impact in this field. Furthermore, in identification of an appropriate starting Kondo system and the best elements for substitution, theoretical prediction may play an important role. For instance, band-structure calculation with respect to a specific Kondo system could predict the suitable elements that might give rise to an ideal TE optimization as observed in the present system.

We thank N. Oeschler for helpful discussions.

*Present address: Max Planck Institute for Chemical Physics of Solids, Dresden 01187, Germany.

†Corresponding author; isikawa@sci.u-toyama.ac.jp

¹G. D. Mahan, *Solid State Phys.* **51**, 81 (1997).

²For cryogenic application, investigations on narrow-gap semiconductors following this concept only found moderately enhanced zT (<0.6) at around 100 K in n -type Bi-Sb alloys (see Ref. 1).

³S. Paschen, in *Thermoelectric Handbook*, edited by D. M. Rowe (CRC Press, Boca Raton, 2006), Chap. 15.

⁴G. Mahan, B. Sales, and J. Sharp, *Phys. Today* **50** (3), 42 (1997).

⁵G. D. Mahan and J. O. Sofo, *Proc. Natl. Acad. Sci. U.S.A.* **93**, 7436 (1996).

⁶R. J. Cava, A. P. Ramirez, H. Takagi, J. J. Krajewski, and W. F. Peck, Jr., *J. Magn. Magn. Mater.* **128**, 124 (1993).

⁷Y. Isikawa, H. Sakai, T. Mizushima, T. Kuwai, and J. Sakurai, *Physica B* **312-313**, 259 (2002).

⁸M. Coldea, M. Neumann, V. Pop, and M. Demeter, *J. Alloys Compd.* **323-324**, 431 (2001).

⁹Q. Lu, P. Sun, D. Huo, T. Mizushima, Y. Isikawa, and J. Sakurai, *J. Phys. Soc. Jpn.* **73**, 681 (2004).

¹⁰ CeCuAl_3 is a heavy-fermion antiferromagnetic ($T_N=2.5$ K) compound. See, for example, M. Kontani, H. Ido, H. Ando, T. Nishioka, and Y. Yamaguchi, *J. Phys. Soc. Jpn.* **63**, 1652 (1994).

¹¹This type of phase transition occurring at zero temperature is usually referred to as quantum critical transition.

¹²K. Behnia, D. Jaccard, and J. Flouquet, *J. Phys.: Condens. Matter* **16**, 5187 (2004).

¹³J. Sakurai and Y. Isikawa, *J. Phys. Soc. Jpn.* **74**, 1926 (2005).

¹⁴The corresponding Cu-substituted nonmagnetic system LaNi_2Al_3 was not studied. Instead, replacement of Pd in the isostructural and isoelectronic system LaPd_2Al_3 by Ag and Cu reveals the similar effects, i.e., reduction in resistivity and γ with increasing Cu/Ag concentration.

¹⁵P. Sun, Q. Lu, K. Kobayashi, T. Kuwai, and Y. Isikawa, *Phys. Rev. B* **70**, 174429 (2004).

¹⁶M. Gomez Berisso, O. Trovarelli, P. Pedrazzini, G. Zwicknagl, C. Geibel, F. Steglich, and J. G. Sereni, *Phys. Rev. B* **58**, 314 (1998).

¹⁷N. Oeschler, S. Hartmann, U. Köhler, M. Deppe, P. Sun, and F. Steglich, in *Properties and Applications of Thermoelectric Materials*, edited by V. Zlatic and A. C. Hewson (Springer, New York, 2009), pp. 81–90.

¹⁸J. Kitagawa, T. Sasakawa, T. Suemitsu, Y. Echizen, and T. Takabatake, *Phys. Rev. B* **66**, 224304 (2002).

¹⁹C. Grenzebach, F. B. Anders, G. Czycholl, and T. Pruschke, *Phys. Rev. B* **74**, 195119 (2006).

²⁰D. Huo, J. Sakurai, O. Maruyama, T. Kuwai, and Y. Isikawa, *J. Magn. Magn. Mater.* **226-230**, 202 (2001).

²¹M. S. Dresselhaus and J. P. Heremans, in *Thermoelectric Handbook*, edited by D. M. Rowe (CRC Press, Boca Raton, 2006), Chap. 39.